Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Surface-mountable package
- Triggering in all four quadrants

1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see Figure 4; see Figure 5	-	-	8	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	1	Α



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } T_j}$	-	-	10	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } T_j}$	-	-	10	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ C}}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ C}}$	-	-	10	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N I
2	T2	main terminal 2	4	T2T1
3	G	gate		`G sym051
4	T2	main terminal 2	1 2 3	
			SOT223 (SOT223)	

3. Ordering information

Table 3. Ordering information

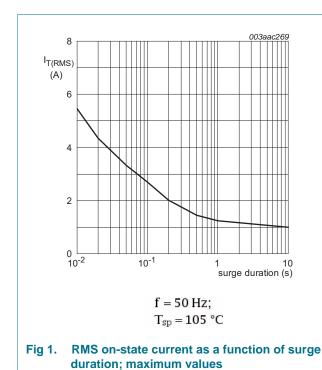
Type number	Package		
	Name	Description	Version
Z0109NN	SOT223	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	1	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	8	Α
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	8.5	Α
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.32	A^2s
dI _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.1 A/ μ s; T2+ G+	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.1 A/ μ s; T2+ G-	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.1 \text{ A/}\mu\text{s}$; T2- G-	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.1 \text{ A/}\mu\text{s}$; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
Γ _{stg}	storage temperature		-40	150	°C
Γ _i	junction temperature		-	125	°C



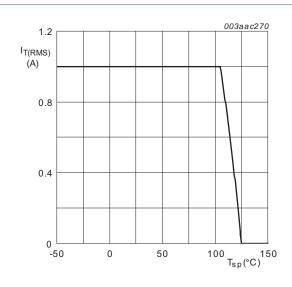
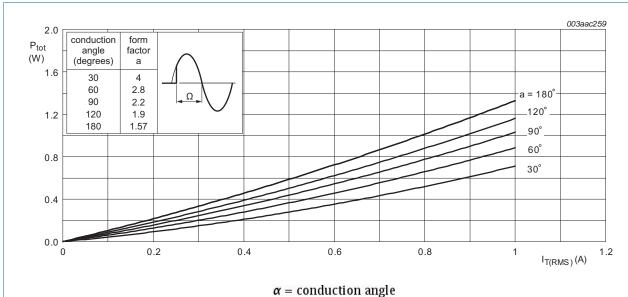


Fig 2. RMS on-state current as a function of solder point temperature; maximum values

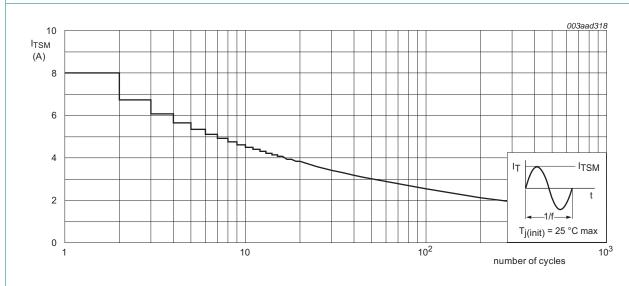
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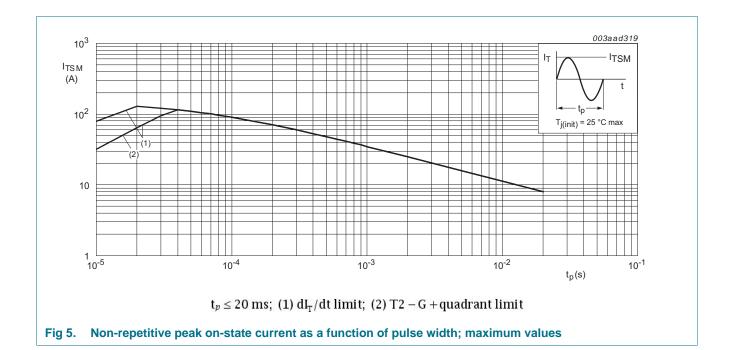
u = conduction angle

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

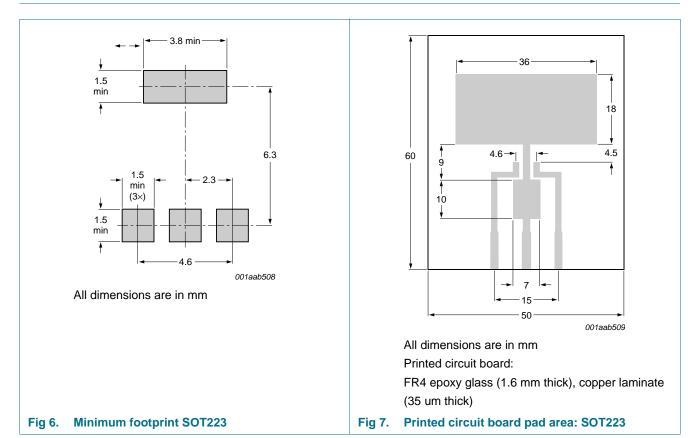


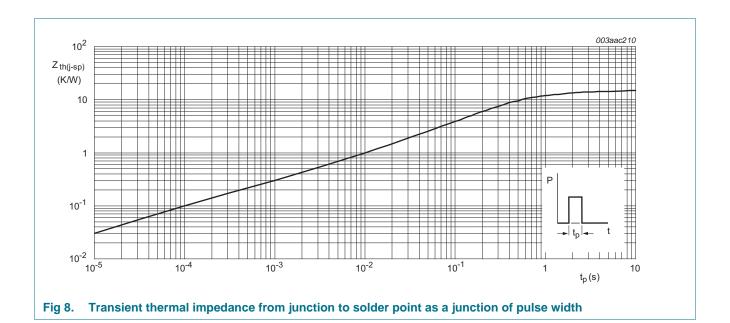
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; see Figure 8	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	full cycle; printed circuit board mounted; minimum footprint; see Figure 6	-	156	-	K/W
	ambient	full cycle; printed circuit board mounted; pad area; see Figure 7	-	70	-	K/W





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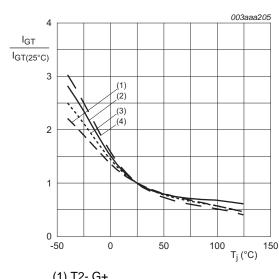
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G+;$ $T_j = 25 ^{\circ}\text{C; see } \frac{\text{Figure 9}}{}$	-	-	10	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	-	15	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 10}{}$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{}$	-	-	15	mA
Н	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ J}}$	-	-	10	mΑ
/ _T	on-state voltage	$I_T = 1.4 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	1.3	1.6	V
/ _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	-	1.3	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C};$ see <u>Figure 13</u>	0.2	-	-	V
D	off-state current	V _D = 800 V; T _j = 125 °C	-	-	0.5	mΑ
Dynamic (characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; gate open circuit; exponential waveform; see Figure 14	50	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 110 ^{\circ}\text{C};$ $dl_{com}/dt = 0.44 \text{ A/ms}; \text{ gate open circuit}$	2	-	-	V/µs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 9. Normalized gate trigger current as a function of junction temperature

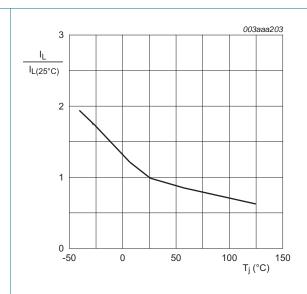


Fig 10. Normalized latching current as a function of junction temperature

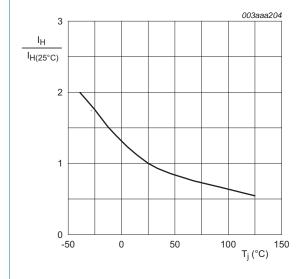
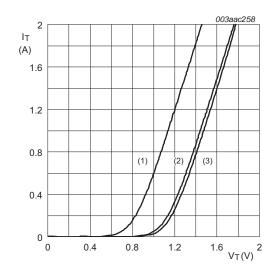


Fig 11. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$

 $R_s = 0.31 \Omega$

(1) T_j = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 12. On-state current as a function of on-state voltage

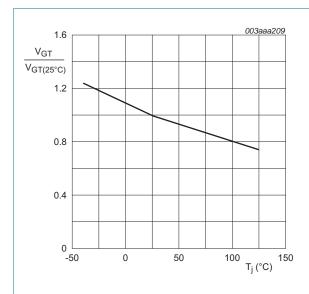


Fig 13. Normalized gate trigger voltage as a function of junction temperature

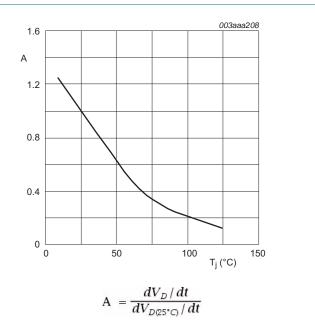


Fig 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

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Package outline Plastic surface-mounted package with increased heatsink; 4 leads **SOT223** В - A = v M A a **→** | w (M) B detail X е 4 mm scale **DIMENSIONS** (mm are the original dimensions) \mathbf{H}_{E} UNIT A_1 $\mathbf{b}_{\mathbf{p}}$ b₁ С Ε Q е e₁ L_p у 0.10 0.80 0.32 0.95 2.3 4.6 0.2 0.1 0.1 1.5 0.01 0.60 2.9 3.3 REFERENCES OUTLINE VERSION EUROPEAN **ISSUE DATE PROJECTION** IEC **JEDEC** JEITA 04-11-10 SOT223 SC-73

Fig 15. Package outline SOT223 (SOT223)

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06-03-16

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0109NN v.5	20110318	Product data sheet	-	Z0109NN v.4
Modifications:	 Various change 	es to content.		
Z0109NN v.4	20100906	Product data sheet	-	Z0109NN v.3

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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